

IS4N46
IS4N45



**LOW INPUT CURRENT
DARLINGTON OUTPUT OPTICALLY
COUPLED ISOLATOR**

APPROVALS

- UL recognised, File No. E91231

DESCRIPTION

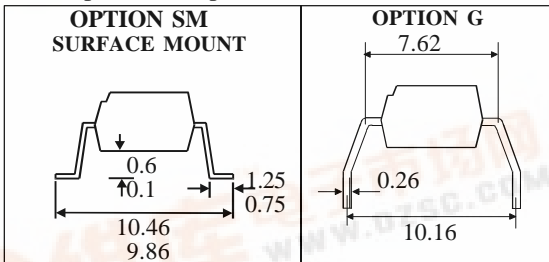
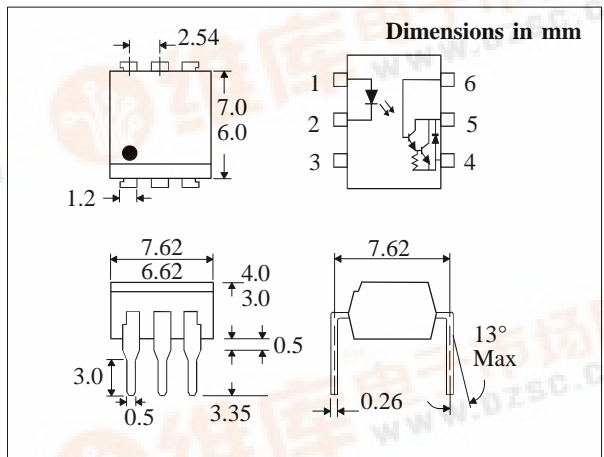
The IS4N45, IS4N46 are optically coupled isolators consisting of an infrared light emitting diode and a NPN silicon photo darlington which has an integral base-emitter resistor to optimise switching speed and elevated temperature characteristics in a standard 6pin dual in line plastic package. These devices are designed to equal the 4N45, 4N46 characteristics while providing greater voltage and current capability.

FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- High Current Transfer Ratio (1500% typ.)
- High BV_{CEO} (55V min.)
- Internal base-emitter resistor minimizes output leakage
- Low input current 0.5mA I_F

APPLICATIONS

- Telephone ring detector
- Digital logic ground isolation
- Low input current line receiver
- Logic to reed relay interface
- Level shifting
- Interface between logic families
- Line voltage status indicator - low input power dissipation



**ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)**

| | |
|-------------------------------------------------------------------------|------------------|
| Storage Temperature | -55°C to + 150°C |
| Operating Temperature | -55°C to + 100°C |
| Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs) | 260°C |

INPUT DIODE

| | |
|---------------------------------------------|-------|
| Forward Current | 60mA |
| Reverse Voltage | 6V |
| Peak Forward Current (1µs pulse, 300pps) | 3A |
| Power Dissipation | 100mW |

OUTPUT TRANSISTOR

| | |
|---------------------------------------------|-------|
| Output Voltage (pin 5 - 4) V _O | 55V |
| Emitter-base Voltage (pin 4 - 6) | 7V |
| Power Dissipation | 200mW |

POWER DISSIPATION

| | |
|-------------------------|-------|
| Total Power Dissipation | 260mW |
|-------------------------|-------|

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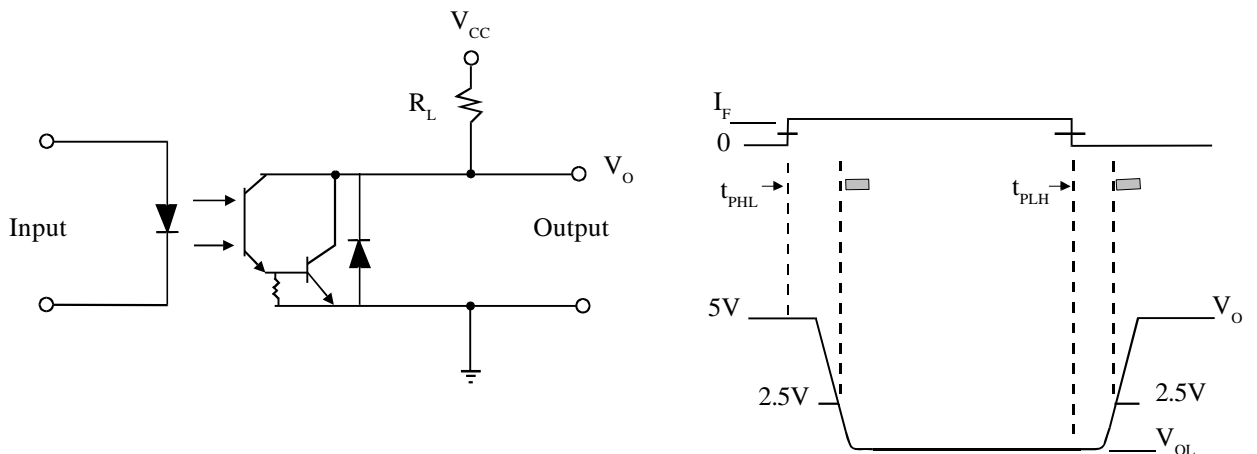
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

| PARAMETER | | MIN | TYP | MAX | UNITS | TEST CONDITION |
|---------------------------------------------|---------------------------------------------|------|-----|-----|---------------|------------------------------------------------------------------------|
| Input | Forward Voltage (V_F) | | 1.2 | 1.5 | V | $I_F = 10\text{mA}$ $I_R = 10\mu\text{A}$ $V_R = 6\text{V}$ |
| | Reverse Voltage (V_R) | 6 | | | V | |
| | Reverse Current (I_R) | | | 10 | μA | |
| Output | Output Breakdown Voltage (pin 5 - 4) | 55 | | | V | $I_{54} = 1\text{mA}$ $I_E = 0.1\text{mA}$ $V_{54} = 18\text{V}$ |
| | Base Breakdown (pin 4 - 6) | 7 | | | V | |
| | Logic High Output | | | 100 | μA | |
| Coupled | DC Current Transfer Ratio (CTR) | | | | | |
| | IS4N46 | 350 | | | % | $0.5\text{mA } I_F, 1\text{V } V_{CE}$ |
| | IS4N46 | 500 | | | % | $1\text{mA } I_F, 1\text{V } V_{CE}$ |
| | IS4N45 | 250 | | | % | $1\text{mA } I_F, 1\text{V } V_{CE}$ |
| | IS4N46, IS4N45 | 200 | | | % | $10\text{mA } I_F, 1.2\text{V } V_{CE}$ |
| | Logic Low Output Voltage (V_{OL}) | | | | | |
| | IS4N46 | | | 1.0 | V | $0.5\text{mA } I_F, 1.75\text{mA } I_{OL}$ |
| | IS4N46 | | | 1.0 | V | $1\text{mA } I_F, 5\text{mA } I_{OL}$ |
| | IS4N45 | | | 1.0 | V | $1\text{mA } I_F, 2.5\text{mA } I_{OL}$ |
| | IS4N46, IS4N45 | | | 1.2 | V | $10\text{mA } I_F, 20\text{mA } I_{OL}$ |
| | Input to Output Isolation Voltage V_{ISO} | 5300 | | | | V_{RMS} |
| | 7500 | | | | V_{PK} | See note 1 |
| Input-output Isolation Resistance R_{ISO} | 10^{11} | | | | Ω | $V_{IO} = 500\text{V}$ (note 1) |
| Input-output Capacitance C_f | | 0.5 | | | pF | $V = 0, f = 1\text{MHz}$ |

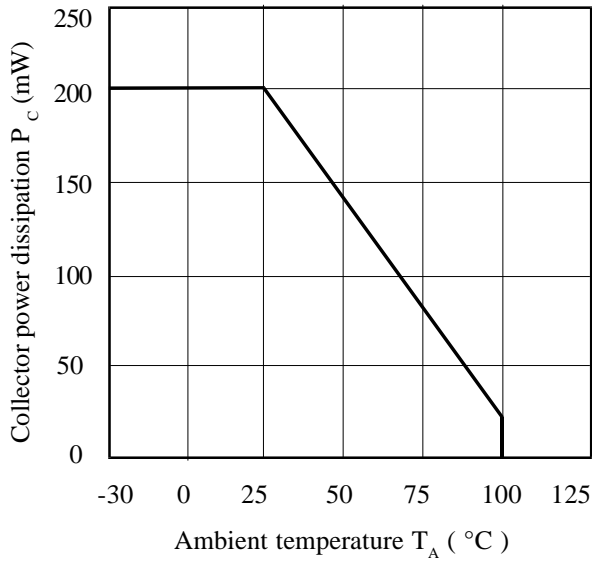
SWITCHING SPECIFICATIONS AT $T_A = 25^\circ\text{C}$ ($V_{CC} = 5\text{V}$ Unless otherwise noted)

| PARAMETER | SYM | DEVICE | MIN | TYP | MAX | UNITS | TEST CONDITION |
|-----------------------------------------------------------|-----------|-----------|-----|------|-----|------------------|------------------------------------------------------------------------------------|
| Propagation Delay Time to Logic Low at Output (fig.1) | t_{PHL} | IS4N46,45 | | 80 | | μs | $I_F = 1\text{mA}, R_L = 10\text{k}\Omega$ $I_F = 10\text{mA}, R_L = 220\Omega$ |
| | t_{PHL} | IS4N46,45 | | 5 | 50 | μs | |
| Propagation Delay Time to Logic High at Output(fig.1) | t_{PLH} | IS4N46,45 | | 1500 | | μs | $I_F = 1\text{mA}, R_L = 10\text{k}\Omega$ $I_F = 10\text{mA}, R_L = 220\Omega$ |
| | t_{PLH} | IS4N46,45 | | 150 | 500 | μs | |
| Common Mode Transient Immunity at Logic High Level Output | CM_H | | | 500 | | V/ μs | $I_F = 0\text{mA}, V_{CM} = 10V_{PP}$ $R_L = 10\text{k}\Omega$ |
| Common Mode Transient Immunity at Logic Low Level Output | CM_L | | | 500 | | V/ μs | $I_F = 1\text{mA}, V_{CM} = 10V_{PP}$ $R_L = 10\text{k}\Omega$ |

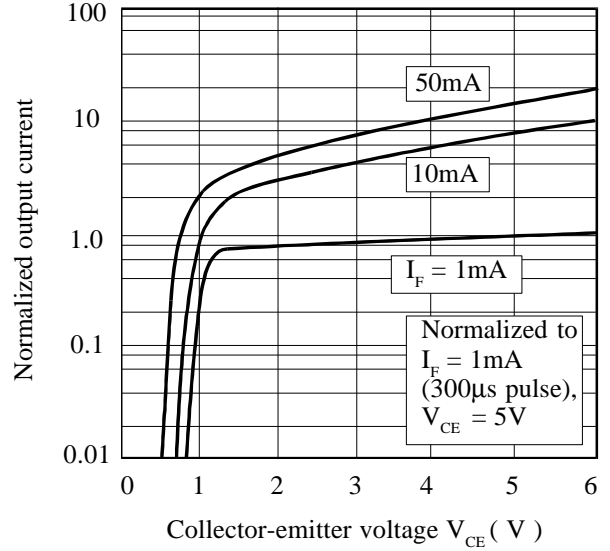
FIGURE 1



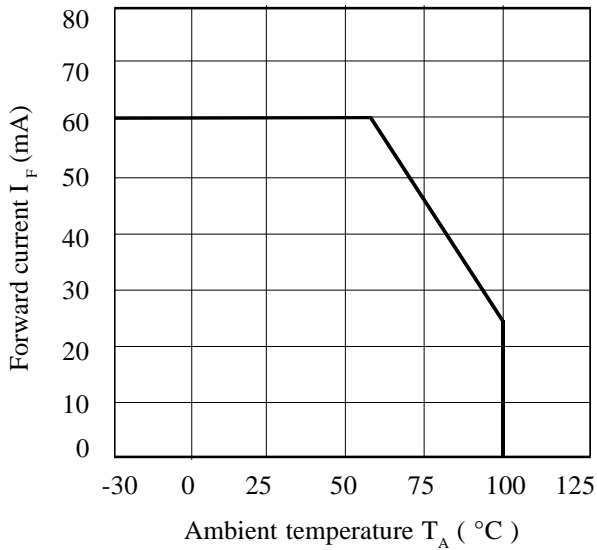
Collector Power Dissipation vs. Ambient Temperature



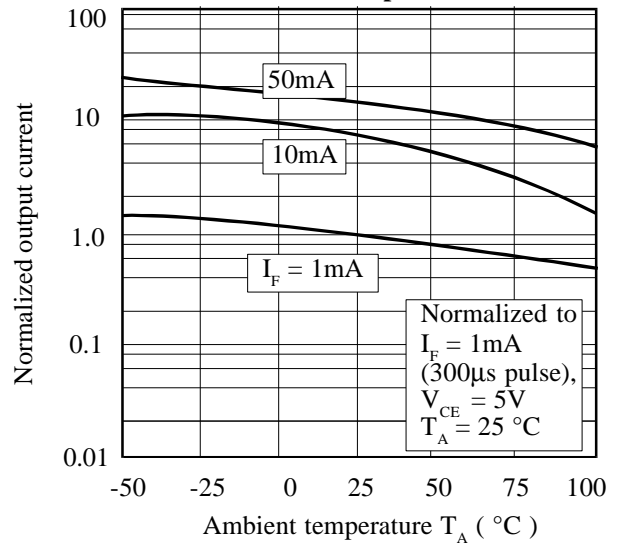
Normalized Output Current vs. Collector-emitter Voltage



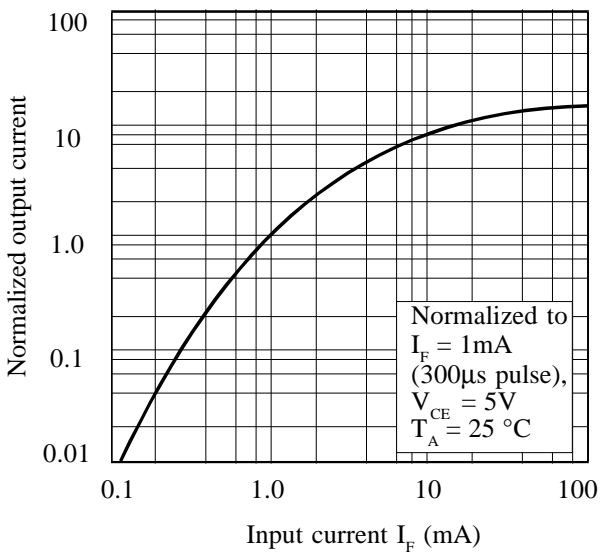
Forward Current vs. Ambient Temperature



Normalized Output Current vs. Ambient Temperature



Normalized Output Current vs. Input Current



Collector Dark Current vs. Ambient Temperature

